

Electronic Supplementary Information (ESI)

Optoelectronic properties of doped Cu-TCNQ nanocrystals

Tsunenobu Onodera,^{*a} Satomi Matsuo,^a Kentaro Hiraishi,^a Akito Masuhara,^b Hitoshi Kasai^a and Hidetoshi Oikawa^a

^a Institute of Multidisciplinary Research for Advanced Materials, Tohoku University, Katahira 2-1-1, Aoba-ku, Sendai 980-8577, Japan. Fax: +81-22-217-5645; Tel: +81-22-217-5645; E-mail: onoderat@tagen.tohoku.ac.jp

^b Graduate School of Science and Technologies, Yamagata University, Jonan 4-3-16, Yonezawa, Japan.

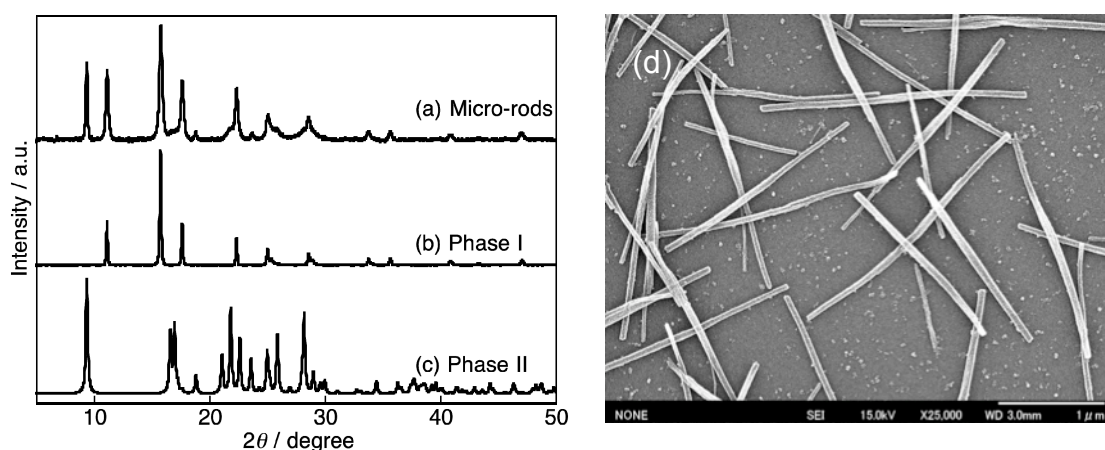


Figure S1 PXR D patterns of (a) Cu-TCNQ micro-rods and (b) Phase I bulk crystal, and simulated pattern of (c) Phase II.^{S1} (d) SEM image of Cu-TCNQ micro-rods corresponding to (a).

Reference

S1. A. Heintz, H. Zhao, X. Ouyang, G. Grandinetti, J. Cowen, and K. R. Dunbar, *Inorg. Chem.*, 1999, **38**, 144-156.